



Solid State Devices, Inc.

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DESIGNER'S DATA SHEET

Part Number / Ordering Information^{1/}
SFT3906A2 — — **Screening**^{2/} ___ = Commercial
 TX = TX Level
 TXV = TXV Level
 S = S Level

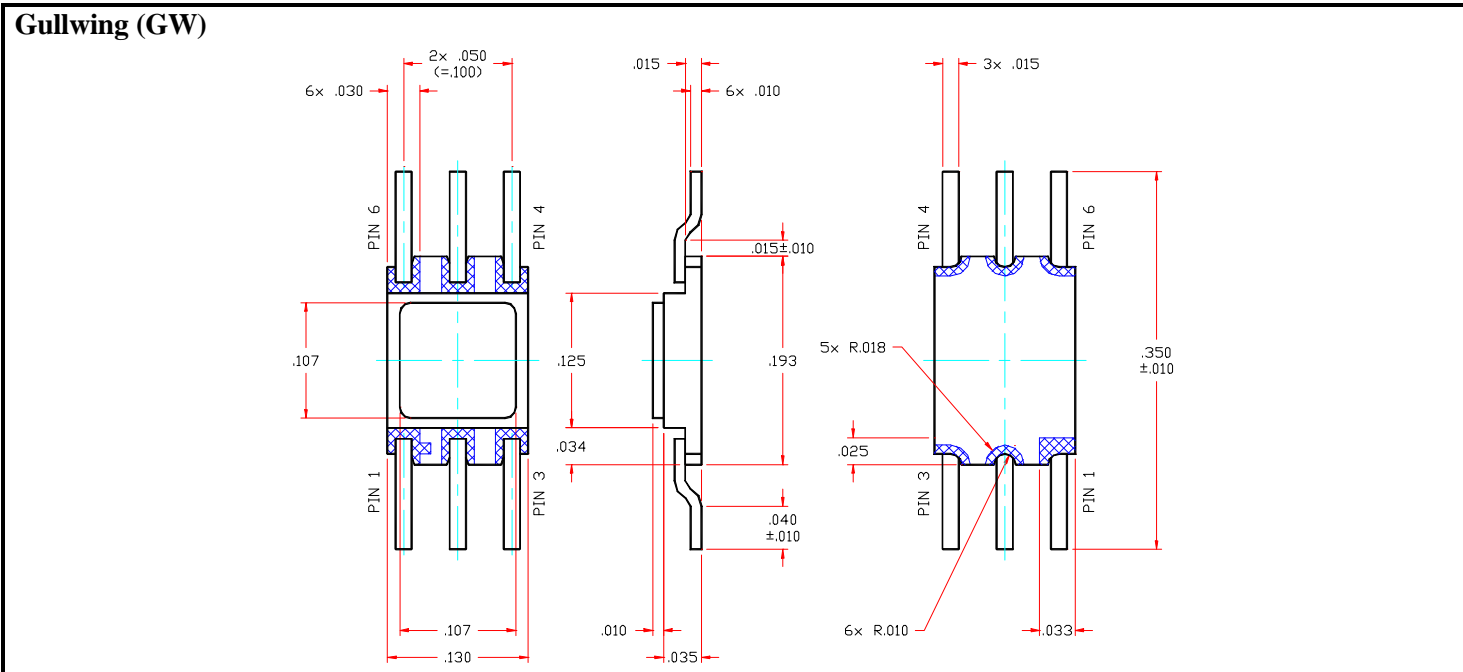
Package GW = Gullwing

SFT3906A2 Series

**Dual Microminiature Package
 800 mA 75 Volts
 Dual PNP Transistor**

- Features:**
- High Speed Switching Transistor
 - Multiple Devices Reduce Board Space
 - High Power Dissipation: Up to 600 mW / device
 - Replacement for 2N3904AU
 - TX, TXV, S-Level screening available
 - NPN complimentary parts available (SFT3904A2)

Maximum Ratings	Symbol	Value	Units
Collector – Emitter Voltage	V _{CEO}	40	Volts
Collector – Base Voltage	V _{CBO}	40	Volts
Emitter – Base Voltage	V _{CBO}	6	Volts
Continues Collector Current	I _C	200	mAmps
Power Dissipation @ TC = 25°C	P _D	600	mW
Operating & Storage Temperature	Top & Tstg	-65 to +200	°C
Maximum Thermal Resistance (Junction to Case)	R _{θJC}	0.29	°C/mW



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: TR0038 A

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SFT3906A2 Series

Electrical Characteristic ^{4/}		Symbol	Min	Max	Units	
Collector – Emitter Sustaining Voltage	$I_C = 1 \text{ mA}$	BV_{CEO}	-40	—	Volts	
Collector – Base Breakdown Voltage	$I_C = 10 \mu\text{A}$	BV_{CBO}	-40	—	Volts	
Emitter – Base Breakdown Voltage	$I_C = 10 \mu\text{A}$	BV_{EBO}	-5	—	Volts	
Collector Cutoff Current	$V_{ce} = -30 \text{ V}, V_{be} = 3.0 \text{ V}$	I_{CEX}	—	50	nA	
Collector Cutoff Current	$V_{cb} = -30 \text{ V}$	I_{CBO}	—	50	nA	
Emitter Cutoff Current	$V_{eb} = -3.0 \text{ V}$	I_{EBO}	—	50	nA	
DC Forward Current Transfer Ratio *	$V_{CE} = -1.0\text{V}, I_C = 0.1 \text{ mA}$ $V_{CE} = -1.0\text{V}, I_C = 1.0 \text{ mA}$ $V_{CE} = -1.0\text{V}, I_C = 10 \text{ mA}$ $V_{CE} = -1.0\text{V}, I_C = 50 \text{ mA}$ $V_{CE} = -1.0\text{V}, I_C = 100 \text{ mA}$	H_{FE}	60 80 100 60 30	— — 300 — —		
Collector – Emitter Saturation Voltage *	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$	$V_{CE(Sat)}$	— —	-0.25 -0.40	Volts	
Base – Emitter Saturation Voltage *	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$	$V_{BE(Sat)}$	-0.65 —	-0.85 -0.95	Volts	
Frequency Transition	$V_{CE} = -20\text{V}, I_C = 20\text{mA}$	f_T	250	—	MHz	
Output Capacitance	$V_{CE} = -10\text{V}, f = 1\text{MHz}$	c_{ob}	—	4.5	pF	
Input Capacitance	$V_{CE} = -0.5\text{V}, f = 1\text{MHz}$	c_{ib}	—	10	pF	
Switch Times	Turn-on Delay Time	$V_{CC} = -3\text{V}, I_C = 10 \text{ mA}$ $I_{B1} = 1\text{mA}, I_{B2} = -1\text{mA}$ $V_{be(off)} = 0.5 \text{ V}$	t_d	—	35	n sec
	Rise Time		t_r	—	35	
	Storage Time		t_s	—	225	
	Fall Time		t_f	—	75	
Small Signal Current Gain ($f = 1 \text{ kHz}$)	$V_{CE} = -10\text{V}, I_C = 1.0 \text{ mA}$	h_{fe}	100	400		
Noise Figure	$I_C = 100 \mu\text{A}, V_{ce} = -5 \text{ V}, R_s = 1.0 \text{ k}\Omega, f = 1 \text{ kHz}$	NF	—	4.0	db	

NOTES:

* Pulse Test: Pulse Width = 300μsec, Duty Cycle = 2%

1/ For Ordering Information, Price, and Availability Contact Factory.

2/ Screening per MIL-PRF-19500

3/ For Package Outlines Contact Factory.

4/ Unless Otherwise Specified, All Electrical Characteristics @25°C.

Available Part Numbers:

SFT3906A2GW

PIN ASSIGNMENT						
Package	Pin 1	Pin 2	Pin 3	Pin 4	Pin 5	Pin 6
GW	Collector1	Base1	Emitter1	Collector2	Base2	Emitter2